128 K x 8/3.3 V Ultimate CMOS SRAM

Introduction

The L65608 is a very low power CMOS static RAM organized as 131072 × 8 bits. It is manufactured using the TEMIC high performance CMOS technology named SCMOS.

The L65608 provides fast access time of 45 ns for a 3 Volts power supply.

Utilizing an array of six transistors (6T) memory cells, the L65608 combines an extremely low standby supply current (Typical value = 0.1 µA) with a fast access time at 45 ns over the full commercial and military temperature range. The high stability of the 6T cell provides excellent protection against soft errors due to noise.

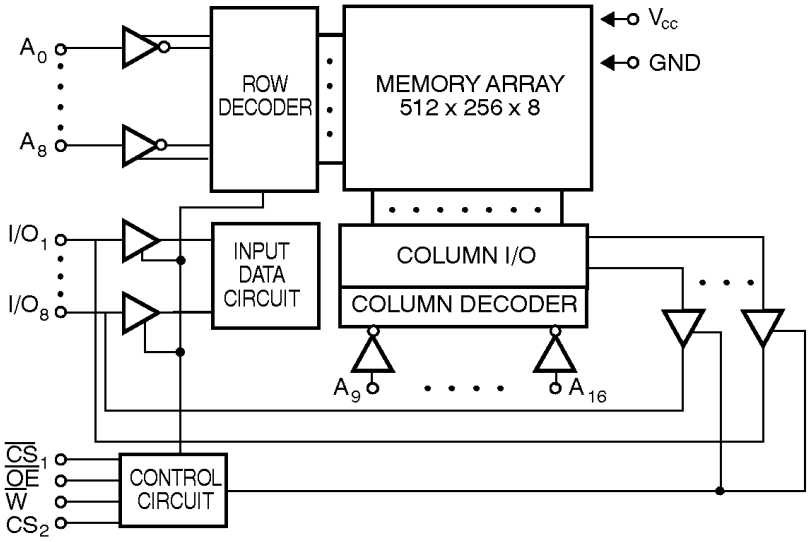
For military/space applications that demand superior levels of performance and reliability the L65608 is processed according to the methods of the latest revision of the MIL STD 883 (class B or S) and/or ESA SCC 9000.

Features

- Single 3.3 ±0.3 volts supply
- Access time : commercial : 45/55/70 ns
  industrial and military : 45/55/70 ns
- Very low power consumption
  active : 150 mW (Typ)
  standby : 0.3 µW (Typ)
  data retention : 0.2 µW (Typ)
- Wide temperature Range : –55 To +125°C
- 400 Mils width package
- TTL compatible inputs and outputs
- Asynchronous
- Equal cycle and access time
- Gated inputs :
  no pull-up/down
  resistors are required

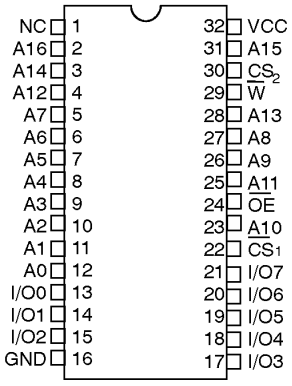
Interface

Block Diagram



Pin Configuration

32 pins DLCC ceramic 400 MILS
32 pins DIL side-brazed 400 MILS
32 pins Flatpack 400 MILS
32 pins PDIL 400 MILS
32 pins SOIC and SOJ 400 MILS



Pin Names

A0–A16	Address inputs
I/O0–I/O7	Data Input/Output
$\overline{CS}_1$	Chip select 1
CS_2	Chip select 2
$\overline{W}$	Write Enable
$\overline{OE}$	Output Enable
V_{CC}	Power
GND	Ground

Truth Table

$\overline{CS}_1$	CS_2	$\overline{W}$	$\overline{OE}$	INPUTS/ OUTPUTS	MODE
H	X	X	X	Z	Deselect/ Power-down
X	L	X	X	Z	Deselect/ Power Down
L	H	H	L	Data Out	Read
L	H	L	X	Data In	Write
L	H	H	H	Z	Output Disable

L = low, H = high, X = H or L, Z = high impedance.

Electrical Characteristics

Absolute Maximum Ratings

Supply voltage to GND potential : . . . . . - 0.5 V + 7.0 V
DC input voltage : . . . . . GND – 0,3 V to VCC + 0,3
DC output voltage high Z state : . . . . . GND – 0,3 V to VCC + 0,3

Storage temperature : . . . . . –65 °C to + 150 °C
Output current into outputs (low) : . . . . . 20 mA
Electro statics discharge voltage : . . . . . > 2 001 V
(MIL STD 883D method 3015.3)

Operating Range

	OPERATING VOLTAGE	OPERATING TEMPERATURE
Military	3.3 V ± 0.3 V	– 55 °C to + 125 °C
Industrial	3.3 V ± 0.3 V	– 40 °C to + 85 °C
Commercial	3.3 V ± 0.3 V	0 °C to + 70 °C

Recommended DC Operating Conditions

PARAMETER	DESCRIPTION	MINIMUM	TYPICAL	MAXIMUM	UNIT
Vcc	Supply voltage	3	3.3	3.6	V
Gnd	Ground	0.0	0.0	0.0	V
VIL	Input low voltage	GND – 0.3	0.0	0.8	V
VIH	Input high voltage	2.2	–	V_{CC} + 0.3	V

Capacitance

PARAMETER	DESCRIPTION	MINIMUM	TYPICAL	MAXIMUM	UNIT
Cin (1)	Input low voltage	–	–	8	pF
Cout (1)	Output high volt	–	–	8	pF

Note : 1. Guaranteed but not tested.

DC Parameters

PARAMETER	DESCRIPTION	MINIMUM	TYPICAL	MAXIMUM	UNIT
IIX (2)	Input leakage current	– 1	–	1	µA
IOZ (2)	Output leakage current	– 1	–	1	µA
VOL (3)	Output low voltage	–	–	0.4	V
VOH (4)	Output high voltage	2.4	–	–	

Notes : 2. Gnd < Vin < Vcc, Gnd < Vout < Vcc Output Disabled.
3. Vcc min. IOL = 6 mA.
4. Vcc min. IOH = –2.0 mA.

Consumption for Commercial

SYMBOL	DESCRIPTION	65608L/V – 45	65608L/V – 55	65608L/V – 70	UNIT	VALUE
ICCSB (5)	Standby supply current	3/1	3/1	3/1	mA	max
$ICCSB_1$ (6)	Standby supply current	400/40	400/40	400/40	µA	max
ICCOP (7)	Dynamic operating current	70/50	65/45	60/40	mA	max

Consumption for Industrial

SYMBOL	DESCRIPTION	65608L/V – 45	65608L/V – 55	65608L/V – 70	UNIT	VALUE
ICCSB (5)	Standby supply current	3/1	3/1	3/1	mA	max
$ICCSB_1$ (6)	Standby supply current	600/80	600/80	600/80	µA	max
ICCOP (7)	Dynamic operating current	70/50	65/45	60/40	mA	max

Consumption for Military

SYMBOL	DESCRIPTION	65608L/V – 45	65608L/V – 55	65608L/V – 70	UNIT	VALUE
ICCSB (5)	Standby supply current	3/1.5	3/1.5	3/1.5	mA	max
$ICCSB_1$ (6)	Standby supply current	800/250	800/250	800/250	µA	max
ICCOP (7)	Dynamic operating current	70/50	65/45	60/40	mA	max

Notes : 5. $\overline{CS}_1 \geq$ VIH or $CS_2 \leq$ VIL and $\overline{CS}_1 \leq$ VIL.
6. $\overline{CS}_1 \geq$ Vcc – 0.3 V or, $CS_2 <$ Gnd + 0.3 V and $\overline{CS}_1 \leq$ 0.2 V
7. F = 1/TAVAV, Iout = 0 mA, $\overline{W}$ = $\overline{OE}$ = VIH, Vin = Gnd/Vcc, Vcc max.

AC Parameters

Input pulse levels : . . . . . Gnd to 3.0 V
Input rise : . . . . . 5 ns
Input timing reference levels : . . . . . 1.5 V
Output loading IOL/IOH (see figure 1a and 1b) : . . . . . + 30 pF

AC Test Loads Waveforms

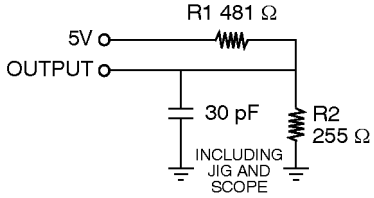


Figure 1a

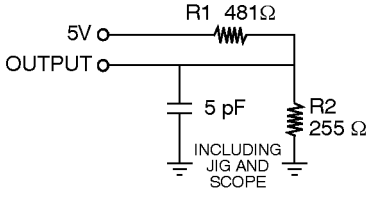


Figure 1b

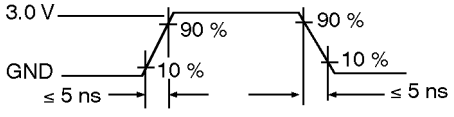
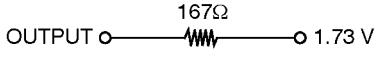


Figure 2

Equivalent to : THEVENIN EQUIVALENT

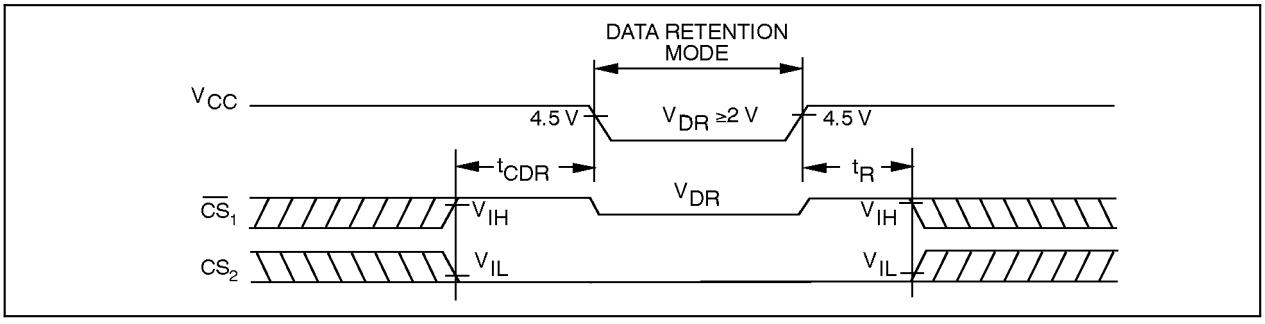


Data Retention Mode

MHS CMOS RAM's are designed with battery backup in mind. Data retention voltage and supply current are guaranteed over temperature. The following rules insure data retention :

1. . During data retention chip select $\overline{CS}_1$ must be held high within VCC to VCC -0.2 V or, chip select CS_2 must be held low within GND to GND + 0.2 V.
2. During power up and power down transitions $\overline{CS}_1$ must be kept between VCC + 0.3 V and 70 % of VCC, or with CS_2 between GND and GND - 0.3 V.
3. The RAM can begin operation > 45 ns after Vcc reaches the minimum operation voltages (4.5 V).

Timing



Data Retention Characteristics

PARAMETER	DESCRIPTION	MINIMUM	TYPICAL T_A = 25 °C	MAXIMUM			UNIT
VCCDR	Vcc for data retention	2.0	–	–			V
TCDR	Chip deselect to data retention time	0.0	–	–			ns
TR	Operation recovery time	TAVAV (9)	–	–			ns
ICCDR1 (10)	Data retention current			COM	IND	MIL	
	@ 2.0 V : L-65608-V	–	0.1	20	40	150	µA
	L-65608-L	–	0.1	200	300	500	µA

Notes : 9. TAVAV = Read cycle time.
10. $\overline{CS}_1$ = Vcc or CS_2 = $\overline{CS}_1$ = GND, Vin = Gnd/Vcc.

Write Cycle

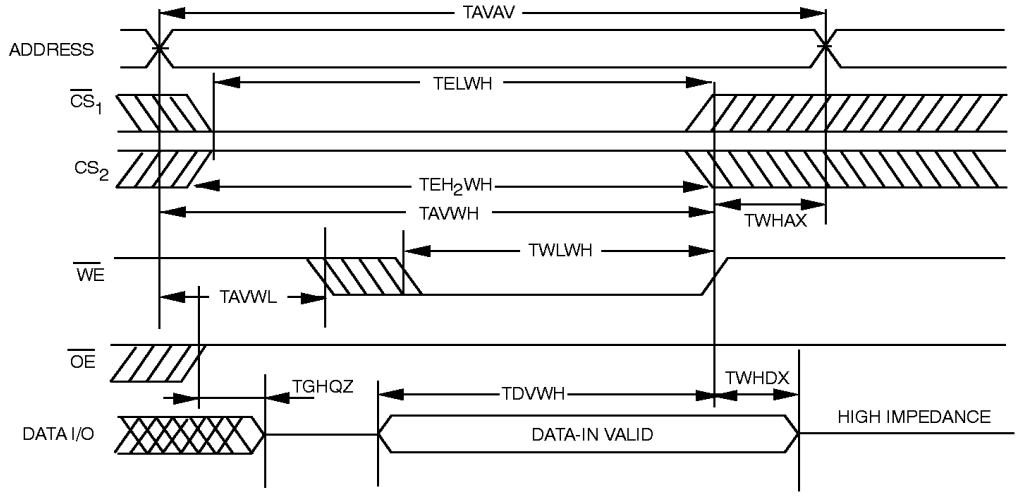
SYMBOL	PARAMETER	65608L/V – 45	65608L/V – 55	65608L/V – 70	UNIT	VALUE
TAVAW	Write cycle time	45	55	70	ns	min
TAVWL	Address set-up time	0	0	0	ns	min
TAVWH	Address valid to end of write	35	45	60	ns	min
TDVWH	Data set-up time	25	35	50	ns	min
TE_1LWH	$\overline{CS}_1$ low to write end	35	45	60	ns	min
TE_2HWH	CS_2 high to write end	35	45	60	ns	min
TWLQZ	Write low to high Z (11)	15	15	20	ns	max
TWLWH	Write pulse width	35	45	60	ns	min
TWHAX	Address hold from to end of write	0	0	0	ns	min
TWHDX	Data hold time	0	0	0	ns	min
TWHQX	Write high to low Z (11)	0	0	0	ns	min

Read Cycle

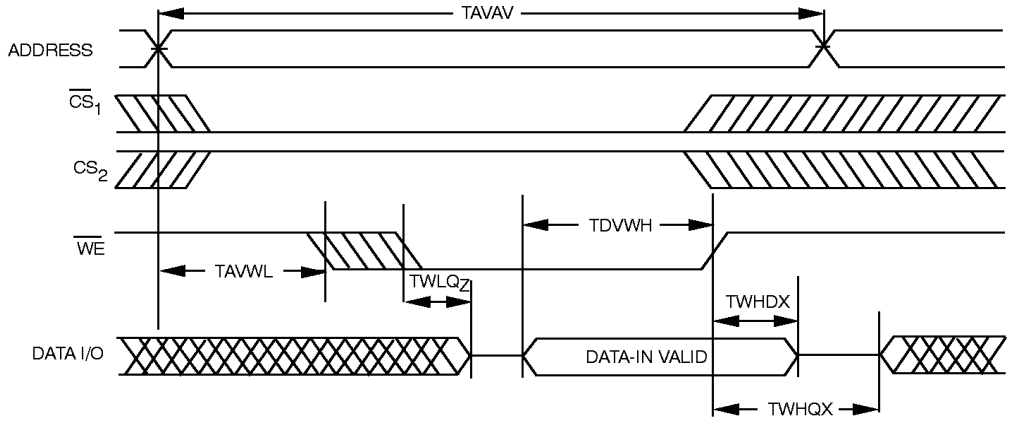
SYMBOL	PARAMETER	65608L/V – 45	65608L/V – 55	65608L/V – 70	UNIT	VALUE
TAVAV	Read cycle time	45	55	70	ns	min
TAVQV	Address access time	45	55	70	ns	max
TAVQX	Address valid to low Z	10	10	10	ns	min
TE_1LQV	Chip-select$_1$ access time	45	55	70	ns	max
TE_1LQX	$\overline{CS}_1$ low to low Z (11)	10	10	10	ns	min
TE_1HQZ	$\overline{CS}_1$ high to high Z (11)	20	20	25	ns	max
TE_2HQV	Chip-select$_2$ access time	45	55	70	ns	max
TE_2HQX	CS_2 high to low Z (11)	10	10	10	ns	min
TE_2LQZ	CS_2 low to high Z (11)	20	20	25	ns	max
TGLQV	Output Enable access time	20	25	30	ns	max
TGLQX	$\overline{OE}$ low to low Z (11)	10	10	10	ns	min
TGHQZ	$\overline{OE}$ high to high Z (11)	15	15	20	ns	max

Notes : 11. Parameters guaranteed, not tested, with output loading 5 pF. (see fig. 1.b.).

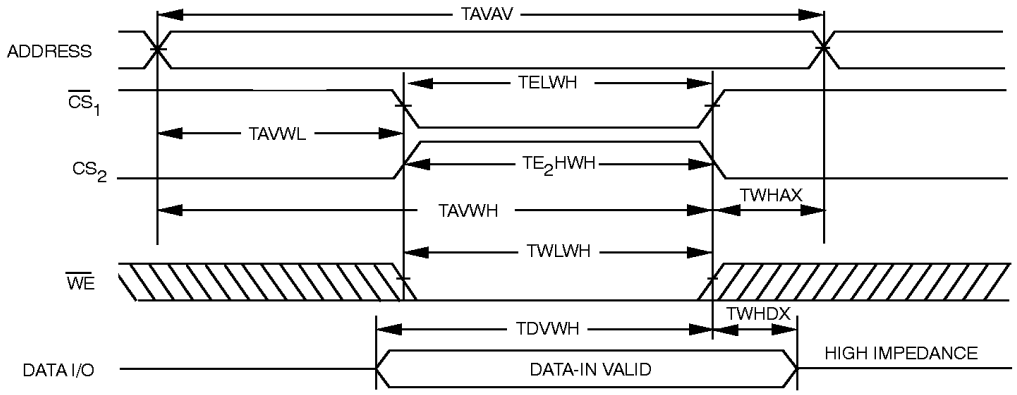
Write Cycle 1. $\overline{W}$ Controlled. $\overline{OE}$ High During Write



Write Cycle 2. $\overline{W}$ Controlled. $\overline{OE}$ Low

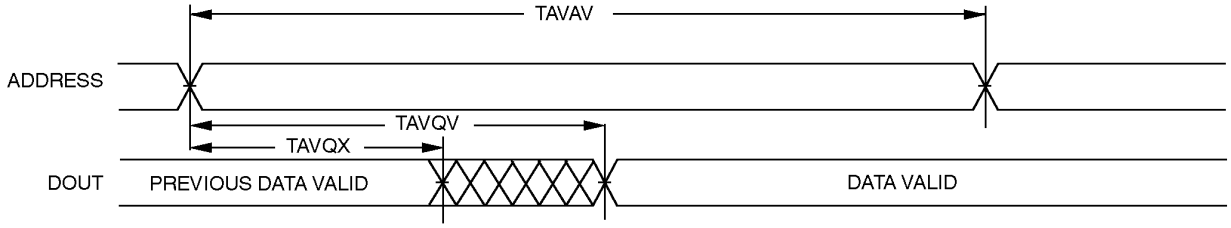


Write Cycle 3. $\overline{CS}_1$ or $\overline{CS}_2$ Controlled.

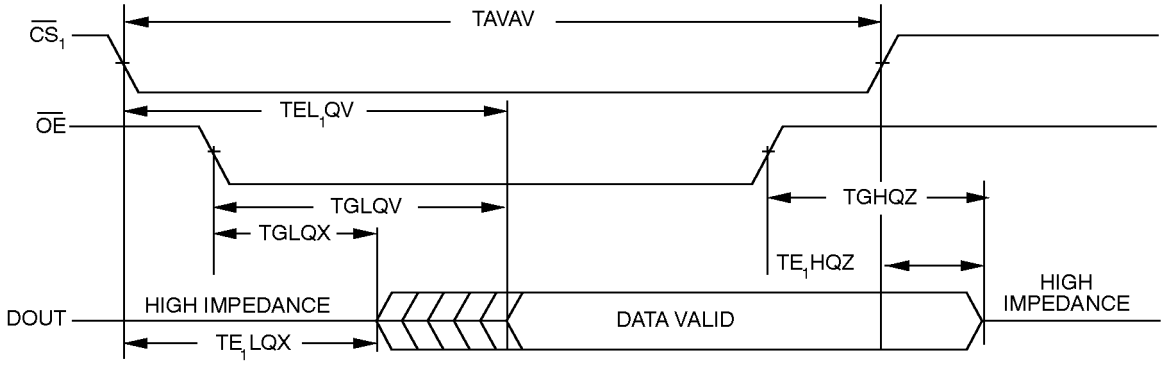


Note : 12. The internal write time of the memory is defined by the overlap of $\overline{CS}_1$ Low and CS_2 HIGH and $\overline{W}$ LOW. Both signals must be actived to initiate a write and either signal can terminate a write by going in actived. The data input setup and hold timing should be referenced to the actived edge of the signal that terminates the write.
Data out is high impedance if $\overline{OE}$ = VIH.

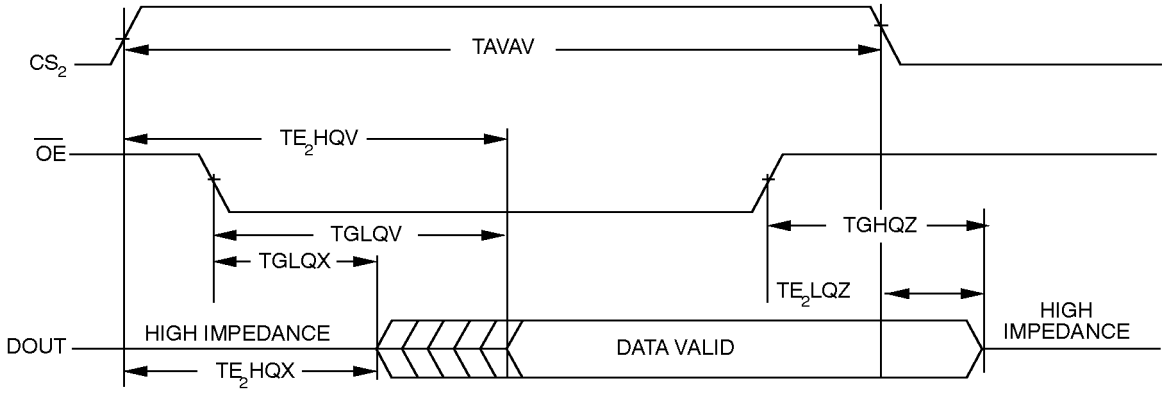
Read Cycle nb 1



Read Cycle nb 2



Read Cycle nb 3



Ordering Information